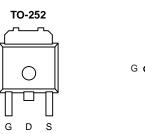
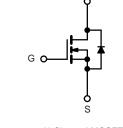


N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a			
60	0.012 at V _{GS} = 10 V	50			
	0.013 at V _{GS} = 4.5 V	45			





N-Channel MOSFET

D

FEATURES

- 175 °C Junction Temperature
- TrenchFET[®] Power MOSFET
- Material categorization:



ABSOLUTE MAXIMUM RATINGS ($T_C =$	25 °C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Desig Connect (T. 175 °C)b	T _C = 25 °C	1	50		
Continuous Drain Current $(T_J = 175 \ ^{\circ}C)^{b}$	T _C = 100 °C	, I _D	45 ^a		
Pulsed Drain Current	I _{DM}	100	А		
Continuous Source Current (Diode Conduction)	۱ _S	50 ^a			
Avalanche Current	I _{AS}	50			
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Dawar Dissinction	T _C = 25 °C	Pn –	136	- w	
Maximum Power Dissipation	T _A = 25 °C		3 ^b , 8.3 ^{b, c}		
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lungting to Ampliant	$t \le 10 \text{ sec}$	R _{thJA}	15	18	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		40	50		
Maximum Junction-to-Case		R _{thJC}	0.85	1.1		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t ≤ 10 s.

Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60		V		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1	2	3	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	1				
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μA	
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	60			А	
	T	V _{GS} = 10 V, I _D = 20 A		0.010	0.012	- Ω	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.016		
Drain-Source On-State Resistance ^b		V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.020		
		V _{GS} = 4.5 V, I _D = 15 A			0.013	1	
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic							
Input Capacitance	C _{iss}			2650		pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		470			
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Qg			47	70		
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_{D} = 50 A		10		nC	
Gate-Drain Charge ^c	Q _{gd}			12		1	
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25	- ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	racteristics (T _C = 25 °C)		<u> </u>			
Pulsed Current	I _{SM}				60	А	
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		45	100	ns	

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

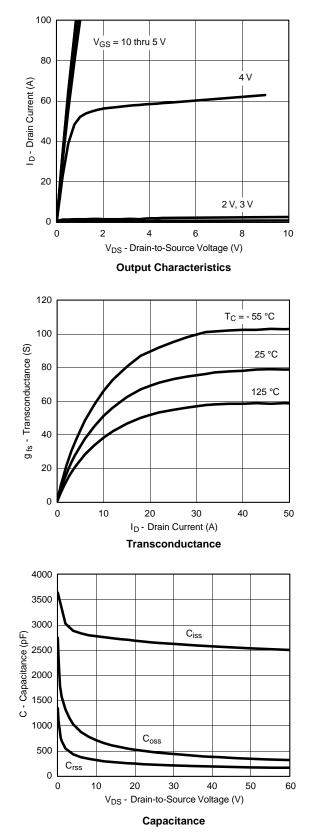
c. Independent of operating temperature.

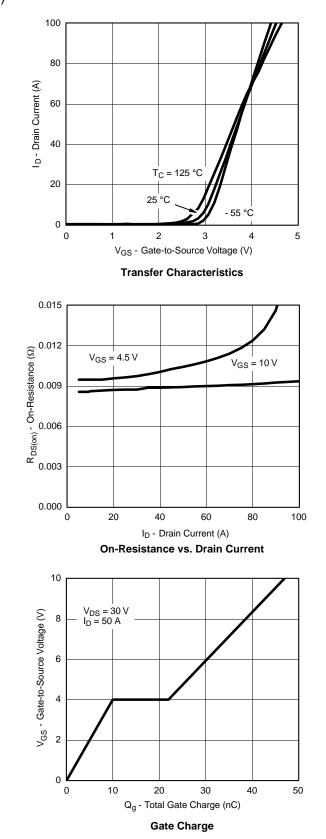
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

emi



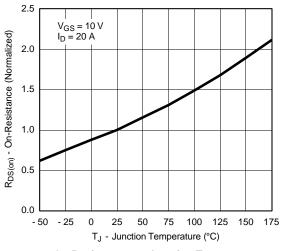
TYPICAL CHARACTERISTICS (25 °C unless noted)



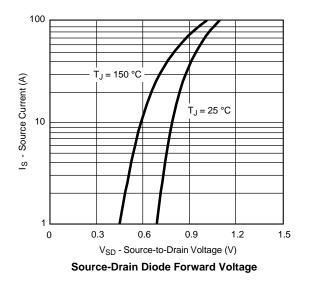




TYPICAL CHARACTERISTICS (25 °C unless noted)



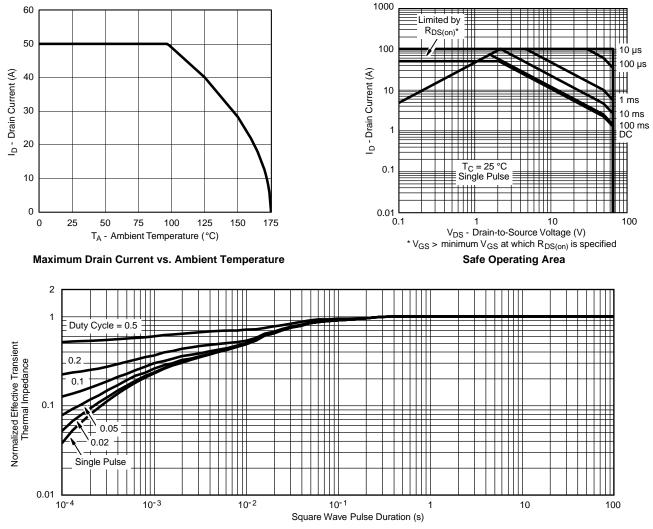
On-Resistance vs. Junction Temperature



CEU50N06



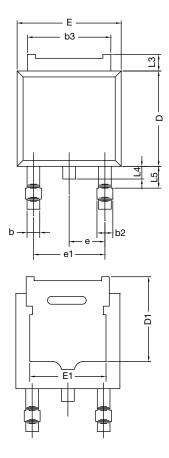
THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12- DWG: 534	0247-Rev. M, 7	24-Dec-12			

Note

• Dimension L3 is for reference only.



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